

REMARKS

Applicants respectfully request reconsideration of this application, as amended.

Without concession as to the propriety of the outstanding rejection, independent Claim 1 has been amended to recite that the plurality of bipolar transistors are provided on the semiconductor layer such that collectors, emitters and bases of the bipolar transistors are respectively connected in parallel with each other. An isolation is provided over a main surface of the semiconductor layer to reach the insulation layer, and provided such that the isolation surrounds a group of or the whole of the plurality of bipolar transistors, such that the surrounded transistor operate substantially uniformly as constituent elements of a unit transistor.

Independent Claim 6 has been amended to recite a plurality of bipolar transistors that are provided on the semiconductor layer such that collectors, emitters and bases of the bipolar transistors are respectively connected in parallel with each other and resistors are electrically connected to corresponding ones of the plurality of bipolar transistors. An isolation is provided over the main surface of the semiconductor layer to reach the insulation layer and

provided such that the isolation surrounds a group of or the whole of the plurality of bipolar transistors, such that the surrounded transistors operate substantially uniformly as constituent elements of a unit transistor.

Independent Claim 10 has been amended to recite a plurality of first bipolar transistors that are provided in a first region over a portion of the semiconductor layer such that collectors of the first bipolar transistors are connected in parallel with each other, emitters of the first bipolar transistors are connected in parallel with each other, and bases of the first bipolar transistors are connected in parallel with each other. A first isolation is provided in the main surface of the semiconductor layer to reach the insulation layer, and provided such that the isolation surrounds a group of or the whole of the plurality of first bipolar transistors in the first region, such that the surrounded first bipolar transistors operate substantially uniformly as constituent elements of a first unit transistor. A plurality of second bipolar transistors are provided in a second region over a portion of the semiconductor layer such that collectors of the second bipolar transistors are connected in parallel with each other, emitters of the second bipolar transistors are

connected in parallel with each other, and bases of the second bipolar transistors are connected in parallel with each other. A second isolation is provided in the main surface of the semiconductor layer to reach the insulation layer, and provided such that the isolation surrounds each the plurality of second bipolar transistors in a second region, such that the surrounded second bipolar transistors operate substantially uniformly as constituent elements of a second unit transistor.

As is readily apparent from the figures of Takashi, the above-enumerated features are neither taught nor suggested. In that the secondary references to Morishita and Moyer fail to overcome the deficiencies of Takashi, the claims are patentably distinguishable therefrom.

Applicants thus respectfully submit that this application is in condition for allowance and should be passed to issue.

An early Notice of Allowance is respectfully requested.

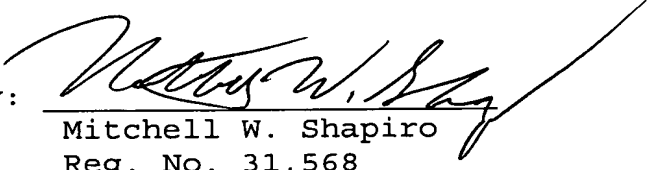
The Commissioner is hereby authorized to charge to Deposit Account No. 50-1165 (XA-10036) any fees under 37 C.F.R. §§ 1.16 and 1.17 that may be required by this paper and to credit any overpayment to that Account. If any

extension of time is required in connection with the filing of this paper and has not been separately requested, such extension is hereby requested.

Respectfully submitted,

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